

## Silicon PNP Power Transistors

2SB849

## DESCRIPTION

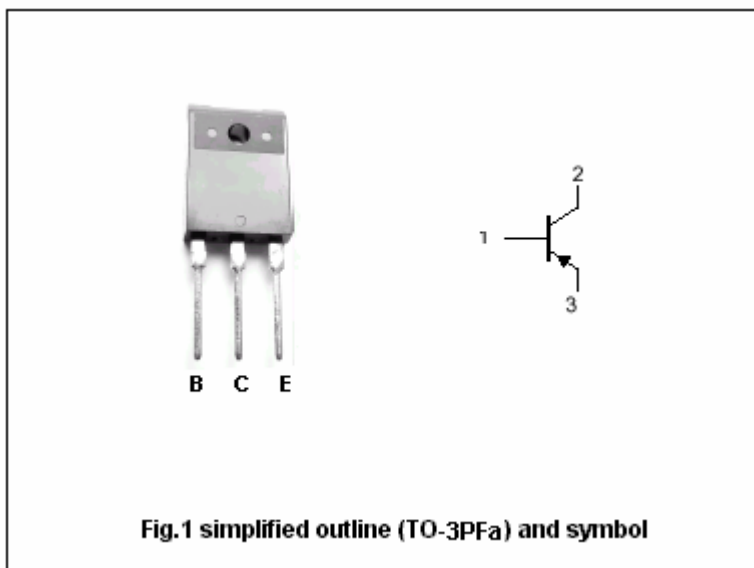
- With TO-3PFa package
- Complement to type 2SD1110
- Wide area of safe operation

## APPLICATIONS

- For use in low frequency power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_a=25$  )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-120	V
$V_{CEO}$	Collector-emitter voltage	Open base	-120	V
$V_{EBO}$	Emitter-base voltage	Open collector	-7	V
$I_C$	Collector current		-7	A
$P_C$	Collector power dissipation	$T_C=25$	80	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(BR)</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-120			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.5A			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.5A			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-120V; I <sub>E</sub> =0			-50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-50	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-20mA ; V <sub>CE</sub> =-5V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	40		200	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V; f=1MHz		340		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.2A ; V <sub>CE</sub> =-5V		14		MHz

PACKAGE OUTLINE

